

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
S1	60927	dielectric adj constant	US-PGPUB; USPAT; EPO; JPO; DERWENT ; IBM_TDB	OR	ON	2004/06/22 13:11
S2	300115	silicone polysiloxane polyorganosiloxane polydiorganosiloxane organopolysiloxane organosiloxane diorganopolysiloxane siloxane organosilicone	US-PGPUB; USPAT; EPO; JPO; DERWENT ; IBM_TDB	OR	ON	2003/12/03 11:50
S3	5087	((dielectric adj constant) and (silicone polysiloxane polyorganosiloxane polydiorganosiloxane organopolysiloxane organosiloxane diorganopolysiloxane siloxane organosilicone)	US-PGPUB; USPAT; EPO; JPO; DERWENT ; IBM_TDB	OR	ON	2004/06/16 11:02
S4	1192	((dielectric adj constant) same (silicone polysiloxane polyorganosiloxane polydiorganosiloxane organopolysiloxane organosiloxane diorganopolysiloxane siloxane organosilicone)	US-PGPUB; USPAT; EPO; JPO; DERWENT ; IBM_TDB	OR	ON	2004/06/22 13:12
S5	57147	silicon adj carbide	US-PGPUB; USPAT; EPO; JPO; DERWENT ; IBM_TDB	OR	ON	2002/02/19 10:55
S6	374	((dielectric adj constant) and (silicone polysiloxane polyorganosiloxane polydiorganosiloxane organopolysiloxane organosiloxane diorganopolysiloxane siloxane organosilicone) and (silicon adj carbide)	US-PGPUB; USPAT; EPO; JPO; DERWENT ; IBM_TDB	OR	ON	2002/02/19 10:55
S7	93	((dielectric adj constant) and (silicone polysiloxane polyorganosiloxane polydiorganosiloxane organopolysiloxane organosiloxane diorganopolysiloxane siloxane organosilicone) and (silicon adj carbide)) and irradiat\$7	US-PGPUB; USPAT; EPO; JPO; DERWENT ; IBM_TDB	OR	ON	2002/02/19 11:02
S8	1330	(silicone polysiloxane polyorganosiloxane polydiorganosiloxane organopolysiloxane organosiloxane diorganopolysiloxane siloxane organosilicone) same (silicon adj carbide)	US-PGPUB; USPAT; EPO; JPO; DERWENT ; IBM_TDB	OR	ON	2002/02/19 11:02
S9	11	((silicone polysiloxane polyorganosiloxane polydiorganosiloxane organopolysiloxane organosiloxane diorganopolysiloxane siloxane organosilicone) same (silicon adj carbide)) same (dielectric adj constant)	US-PGPUB; USPAT; EPO; JPO; DERWENT ; IBM_TDB	OR	ON	2002/02/19 11:07
S10	3	((silicone polysiloxane polyorganosiloxane polydiorganosiloxane organopolysiloxane organosiloxane diorganopolysiloxane siloxane organosilicone) same (silicon adj carbide)) same (dielectric adj constant)) and irradiat\$7	US-PGPUB; USPAT; EPO; JPO; DERWENT ; IBM_TDB	OR	ON	2002/02/19 11:08
S11	4217	irradiat\$7 same (silicone polysiloxane polyorganosiloxane polydiorganosiloxane organopolysiloxane organosiloxane diorganopolysiloxane siloxane organosilicone)	US-PGPUB; USPAT; EPO; JPO; DERWENT ; IBM_TDB	OR	ON	2002/02/19 11:12
S12	1	((irradiat\$7 same (silicone polysiloxane polyorganosiloxane polydiorganosiloxane organopolysiloxane organosiloxane diorganopolysiloxane siloxane organosilicone)) and ((dielectric adj constant) same (silicon adj carbide))	US-PGPUB; USPAT; EPO; JPO; DERWENT ; IBM_TDB	OR	ON	2002/02/19 11:09
S13	3	((irradiat\$7 same (silicone polysiloxane polyorganosiloxane polydiorganosiloxane organopolysiloxane organosiloxane diorganopolysiloxane siloxane organosilicone)) and (dielectric adj constant) and (silicon adj carbide)	US-PGPUB; USPAT; EPO; JPO; DERWENT ; IBM_TDB	OR	ON	2002/02/19 11:09

S14	84	((irradiat\$7 same (silicone polysiloxane polyorganosiloxane polydiorganosiloxane organopolysiloxane organosiloxane diorganopolysiloxane siloxane organosilicone)) and (dielectric adj constant))	US-PGPUB; USPAT; EPO; JPO; DERWENT ; IBM_TDB	OR	ON	2002/02/19 11:13
S15	5496	((irradiat\$7 or (electron adj beam)) same (silicone polysiloxane polyorganosiloxane polydiorganosiloxane organopolysiloxane organosiloxane diorganopolysiloxane siloxane organosilicone))	US-PGPUB; USPAT; EPO; JPO; DERWENT ; IBM_TDB	OR	ON	2002/02/19 11:13
S16	132	((irradiat\$7 or (electron adj beam)) same (silicone polysiloxane polyorganosiloxane polydiorganosiloxane organopolysiloxane organosiloxane diorganopolysiloxane siloxane organosilicone)) and (dielectric adj constant))	US-PGPUB; USPAT; EPO; JPO; DERWENT ; IBM_TDB	OR	ON	2002/02/19 11:13
S17	10	((irradiat\$7 or (electron adj beam)) same (silicone polysiloxane polyorganosiloxane polydiorganosiloxane organopolysiloxane organosiloxane diorganopolysiloxane siloxane organosilicone)) and (dielectric adj constant)) and (silicon adj carbide)	US-PGPUB; USPAT; EPO; JPO; DERWENT ; IBM_TDB	OR	ON	2002/02/19 11:16
S18	122	((irradiat\$7 or (electron adj beam)) same (silicone polysiloxane polyorganosiloxane polydiorganosiloxane organopolysiloxane organosiloxane diorganopolysiloxane siloxane organosilicone)) and (dielectric adj constant)) not (((irradiat\$7 or (electron adj beam)) same (silicone polysiloxane polyorganosiloxane polydiorganosiloxane organopolysiloxane organosiloxane diorganopolysiloxane siloxane organosilicone)) and (dielectric adj constant)) and (silicon adj carbide))	US-PGPUB; USPAT; EPO; JPO; DERWENT ; IBM_TDB	OR	ON	2002/02/19 11:22
S19	0	((irradiat\$7 or (electron adj beam)) same (silicone polysiloxane polyorganosiloxane polydiorganosiloxane organopolysiloxane organosiloxane diorganopolysiloxane siloxane organosilicone)) and (dielectric adj constant)) not (((irradiat\$7 or (electron adj beam)) same (silicone polysiloxane polyorganosiloxane polydiorganosiloxane organopolysiloxane organosiloxane diorganopolysiloxane siloxane organosilicone)) and (dielectric adj constant)) and (silicon adj carbide))) and "si-c-si"	US-PGPUB; USPAT; EPO; JPO; DERWENT ; IBM_TDB	OR	ON	2002/02/19 11:22
S20	1	((irradiat\$7 or (electron adj beam)) same (silicone polysiloxane polyorganosiloxane polydiorganosiloxane organopolysiloxane organosiloxane diorganopolysiloxane siloxane organosilicone)) and (dielectric adj constant)) and "si-c-si"	US-PGPUB; USPAT; EPO; JPO; DERWENT ; IBM_TDB	OR	ON	2003/12/03 11:47
S21	2	((("6177143") or ("6132814"))).PN.	USPAT; USOCR	OR	OFF	2002/02/20 07:48
S22	2	jp-2001015500-\$.did.	US-PGPUB; USPAT; EPO; JPO; DERWENT ; IBM_TDB	OR	ON	2003/12/03 10:58
S23	16	"6207555".pn. "6548899".pn. "6271146".pn. "6582777".pn. "6489225".pn. "6426127".pn. "6358670".pn. "6319655".pn.	US-PGPUB; USPAT; EPO; JPO; DERWENT ; IBM_TDB	OR	ON	2003/12/03 11:02
S24	2	"20030008481"	US-PGPUB; USPAT; EPO; JPO; DERWENT ; IBM_TDB	OR	ON	2003/12/03 11:02
S25	2	"20030102084"	US-PGPUB; USPAT; EPO; JPO; DERWENT ; IBM_TDB	OR	ON	2003/12/03 11:02
S26	20	("6207555".pn. "6548899".pn. "6271146".pn. "6582777".pn. "6489225".pn. "6426127".pn. "6358670".pn. "6319655".pn.) "20030008481" "20030102084"	US-PGPUB; USPAT; EPO; JPO; DERWENT ; IBM_TDB	OR	ON	2003/12/03 11:02

S27	150752	electron adj2 beam	US-PGPUB; USPAT; EPO; JPO; DERWENT ; IBM_TDB	OR	ON	2003/12/03 11:49
S28	3667	(electron adj2 beam) same dielectric	US-PGPUB; USPAT; EPO; JPO; DERWENT ; IBM_TDB	OR	ON	2003/12/03 11:50
S29	353882	silicone polysiloxane polyorganosiloxane polydiorganosiloxane organopolysiloxane organosiloxane diorganopolysiloxane siloxane organosilicone	US-PGPUB; USPAT; EPO; JPO; DERWENT ; IBM_TDB	OR	ON	2003/12/03 11:52
S30	361896	silicone polysiloxane polyorganosiloxane polydiorganosiloxane organopolysiloxane organosiloxane diorganopolysiloxane siloxane organosilicone alkoxysilane silsesquioxane	US-PGPUB; USPAT; EPO; JPO; DERWENT ; IBM_TDB	OR	ON	2003/12/03 12:31
S31	432	((electron adj2 beam) same dielectric) and (silicone polysiloxane polyorganosiloxane polydiorganosiloxane organopolysiloxane organosiloxane diorganopolysiloxane siloxane organosilicone alkoxysilane silsesquioxane)	US-PGPUB; USPAT; EPO; JPO; DERWENT ; IBM_TDB	OR	ON	2003/12/03 12:32
S32	209	((electron adj2 beam) same dielectric) and (silicone polysiloxane polyorganosiloxane polydiorganosiloxane organopolysiloxane organosiloxane diorganopolysiloxane siloxane organosilicone alkoxysilane silsesquioxane)) and (dielectric adj2 constant)	US-PGPUB; USPAT; EPO; JPO; DERWENT ; IBM_TDB	OR	ON	2003/12/03 12:36
S33	4474	(electron or electrons) near5 (dose dosage)	US-PGPUB; USPAT; EPO; JPO; DERWENT ; IBM_TDB	OR	ON	2003/12/03 12:35
S34	49	((electron adj2 beam) same dielectric) and (silicone polysiloxane polyorganosiloxane polydiorganosiloxane organopolysiloxane organosiloxane diorganopolysiloxane siloxane organosilicone alkoxysilane silsesquioxane)) and (dielectric adj2 constant)) and ((electron or electrons) near5 (dose dosage))	US-PGPUB; USPAT; EPO; JPO; DERWENT ; IBM_TDB	OR	ON	2003/12/03 12:36
S35	3477	(electron adj2 beam) and ((electron or electrons) near5 (dose dosage))	US-PGPUB; USPAT; EPO; JPO; DERWENT ; IBM_TDB	OR	ON	2003/12/03 12:36
S36	720	((electron adj2 beam) and ((electron or electrons) near5 (dose dosage))) and (silicone polysiloxane polyorganosiloxane polydiorganosiloxane organopolysiloxane organosiloxane diorganopolysiloxane siloxane organosilicone alkoxysilane silsesquioxane)	US-PGPUB; USPAT; EPO; JPO; DERWENT ; IBM_TDB	OR	ON	2003/12/03 12:36
S37	65	((electron adj2 beam) and ((electron or electrons) near5 (dose dosage))) and (silicone polysiloxane polyorganosiloxane polydiorganosiloxane organopolysiloxane organosiloxane diorganopolysiloxane siloxane organosilicone alkoxysilane silsesquioxane)) and (dielectric adj2 constant)	US-PGPUB; USPAT; EPO; JPO; DERWENT ; IBM_TDB	OR	ON	2003/12/03 12:38
S38	65	((electron adj2 beam) and ((electron or electrons) near5 (dose dosage))) and (silicone polysiloxane polyorganosiloxane polydiorganosiloxane organopolysiloxane organosiloxane diorganopolysiloxane siloxane organosilicone alkoxysilane silsesquioxane)) and ((dielectric adj2 constant) or (dielectric near5 ("k" "low-k" "low k")))	US-PGPUB; USPAT; EPO; JPO; DERWENT ; IBM_TDB	OR	ON	2003/12/03 14:48
S39	2	"6132814".pn.	US-PGPUB; USPAT; EPO; JPO; DERWENT ; IBM_TDB	OR	ON	2003/12/03 14:48

S40	1962	427/226.ccls. 427/227.ccls. 427/228.ccls.	US-PGPUB; USPAT; EPO; JPO; DERWENT ; IBM_TDB	OR	ON	2004/06/16 11:01
S41	12367	((dielectric adj constant) and (silicone polysiloxane polyorganosiloxane polydiorganosiloxane organopolysiloxane organosiloxane diorganopolysiloxane siloxane organosilicone silane organosilane alkoxy silane oxysilane))	US-PGPUB; USPAT; EPO; JPO; DERWENT ; IBM_TDB	OR	ON	2004/06/16 11:03
S42	39	(427/226.ccls. 427/227.ccls. 427/228.ccls.) and ((dielectric adj constant) and (silicone polysiloxane polyorganosiloxane polydiorganosiloxane organopolysiloxane organosiloxane diorganopolysiloxane siloxane organosilicone silane organosilane alkoxy silane oxysilane))	US-PGPUB; USPAT; EPO; JPO; DERWENT ; IBM_TDB	OR	ON	2004/06/16 13:09
S43	6	(427/226.ccls. 427/227.ccls. 427/228.ccls.) and ((dielectric adj constant) and (silicone polysiloxane polyorganosiloxane polydiorganosiloxane organopolysiloxane organosiloxane diorganopolysiloxane siloxane organosilicone silane organosilane alkoxy silane oxysilane)) and irradiat\$	US-PGPUB; USPAT; EPO; JPO; DERWENT ; IBM_TDB	OR	ON	2004/06/16 13:11
S44	2310	((dielectric adj constant) and (silicone polysiloxane polyorganosiloxane polydiorganosiloxane organopolysiloxane organosiloxane diorganopolysiloxane siloxane organosilicone silane organosilane alkoxy silane oxysilane)) and irradiat\$	US-PGPUB; USPAT; EPO; JPO; DERWENT ; IBM_TDB	OR	ON	2004/06/16 13:12
S45	91	((dielectric adj constant) and (silicone polysiloxane polyorganosiloxane polydiorganosiloxane organopolysiloxane organosiloxane diorganopolysiloxane siloxane organosilicone silane organosilane alkoxy silane oxysilane)) and (irradiat\$ near3 (dose dosage))	US-PGPUB; USPAT; EPO; JPO; DERWENT ; IBM_TDB	OR	ON	2004/06/16 13:12
S46	20	((dielectric adj constant) and (silicone polysiloxane polyorganosiloxane polydiorganosiloxane organopolysiloxane organosiloxane diorganopolysiloxane siloxane organosilicone silane organosilane alkoxy silane oxysilane)) and (irradiat\$ near3 (dose dosage))) and (carbide "sic" "si-c" "sicsi" "si-c-si" siliconcarbide)	US-PGPUB; USPAT; EPO; JPO; DERWENT ; IBM_TDB	OR	ON	2004/06/16 13:13
S47	87001	dielectric adj constant	US-PGPUB; USPAT; EPO; JPO; DERWENT ; IBM_TDB	OR	ON	2004/09/15 10:30
S48	55063	(silicone polysiloxane polyorganosiloxane polydiorganosiloxane organopolysiloxane organosiloxane diorganopolysiloxane siloxane organosilicone) same film	US-PGPUB; USPAT; EPO; JPO; DERWENT ; IBM_TDB	OR	ON	2004/06/22 13:12
S49	134780	silane organosilane alkoxy silane oxysilane	US-PGPUB; USPAT; EPO; JPO; DERWENT ; IBM_TDB	OR	ON	2004/06/22 13:13
S50	893	((dielectric adj constant) and ((silicone polysiloxane polyorganosiloxane polydiorganosiloxane organopolysiloxane organosiloxane diorganopolysiloxane siloxane organosilicone) same film) and (silane organosilane alkoxy silane oxysilane))	US-PGPUB; USPAT; EPO; JPO; DERWENT ; IBM_TDB	OR	ON	2004/06/22 13:12
S51	148521	silane organosilane alkoxy silane oxysilane \$15alkoxy silane \$15methoxy silane \$15ethoxy silane \$15propoxy silane disilane methoxy silane ethoxy silane propoxy silane \$15organosilane	US-PGPUB; USPAT; EPO; JPO; DERWENT ; IBM_TDB	OR	ON	2004/06/22 13:29
S52	149278	silane organosilane alkoxy silane oxysilane \$20alkoxy silane \$20methoxy silane \$20ethoxy silane \$20propoxy silane disilane methoxy silane ethoxy silane propoxy silane \$20organosilane	US-PGPUB; USPAT; EPO; JPO; DERWENT ; IBM_TDB	OR	ON	2004/06/22 13:31

S53	986	((dielectric adj constant) and ((silicone polysiloxane polyorganosiloxane polydiorganosiloxane organopolysiloxane organosiloxane diorganopolysiloxane siloxane organosilicone) same film) and (silane organosilane alkoxyisilane oxysilane \$20alkoxyisilane \$20methoxyisilane \$20ethoxyisilane \$20propoxyisilane disilane methoxyisilane ethoxyisilane propoxyisilane \$20organosilane)	US-PGPUB; USPAT; EPO; JPO; DERWENT ; IBM_TDB	OR	ON	2004/06/22 13:32
S54	159197	electron adj2 beam	US-PGPUB; USPAT; EPO; JPO; DERWENT ; IBM_TDB	OR	ON	2004/06/22 13:32
S55	209	((dielectric adj constant) and ((silicone polysiloxane polyorganosiloxane polydiorganosiloxane organopolysiloxane organosiloxane diorganopolysiloxane siloxane organosilicone) same film) and (silane organosilane alkoxyisilane oxysilane \$20alkoxyisilane \$20methoxyisilane \$20ethoxyisilane \$20propoxyisilane disilane methoxyisilane ethoxyisilane propoxyisilane \$20organosilane)) and (electron adj2 beam)	US-PGPUB; USPAT; EPO; JPO; DERWENT ; IBM_TDB	OR	ON	2004/06/22 13:32
S56	6344	(electron adj2 beam) same (dose dosage)	US-PGPUB; USPAT; EPO; JPO; DERWENT ; IBM_TDB	OR	ON	2004/09/15 10:28
S57	32	((dielectric adj constant) and ((silicone polysiloxane polyorganosiloxane polydiorganosiloxane organopolysiloxane organosiloxane diorganopolysiloxane siloxane organosilicone) same film) and (silane organosilane alkoxyisilane oxysilane \$20alkoxyisilane \$20methoxyisilane \$20ethoxyisilane \$20propoxyisilane disilane methoxyisilane ethoxyisilane propoxyisilane \$20organosilane)) and ((electron adj2 beam) same (dose dosage))	US-PGPUB; USPAT; EPO; JPO; DERWENT ; IBM_TDB	OR	ON	2004/06/22 13:37
S58	644110	(semiconductor (semi adj conductor)) near5 device	US-PGPUB; USPAT; EPO; JPO; DERWENT ; IBM_TDB	OR	ON	2004/06/22 13:37
S59	122	((dielectric adj constant) and ((silicone polysiloxane polyorganosiloxane polydiorganosiloxane organopolysiloxane organosiloxane diorganopolysiloxane siloxane organosilicone) same film) and (silane organosilane alkoxyisilane oxysilane \$20alkoxyisilane \$20methoxyisilane \$20ethoxyisilane \$20propoxyisilane disilane methoxyisilane ethoxyisilane propoxyisilane \$20organosilane)) and (electron adj2 beam)) and ((semiconductor (semi adj conductor)) near5 device)	US-PGPUB; USPAT; EPO; JPO; DERWENT ; IBM_TDB	OR	ON	2004/06/22 13:38
S60	22	((dielectric adj constant) and ((silicone polysiloxane polyorganosiloxane polydiorganosiloxane organopolysiloxane organosiloxane diorganopolysiloxane siloxane organosilicone) same film) and (silane organosilane alkoxyisilane oxysilane \$20alkoxyisilane \$20methoxyisilane \$20ethoxyisilane \$20propoxyisilane disilane methoxyisilane ethoxyisilane propoxyisilane \$20organosilane)) and ((electron adj2 beam) same (dose dosage))) and ((semiconductor (semi adj conductor)) near5 device)	US-PGPUB; USPAT; EPO; JPO; DERWENT ; IBM_TDB	OR	ON	2004/06/22 16:37
S61	2	"6207555".pn.	US-PGPUB; USPAT; EPO; JPO; DERWENT ; IBM_TDB	OR	ON	2004/06/22 16:38
S62	32	shiota-atsushi.in. shiota-atsushi-\$.in. atsushi-shiota.in. atsushi-shiota-\$.in. sumiya-kouji.in. sumiya-kouji-\$.in. kouji-sumiya.in. kouji-sumiya-\$.in.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT ; IBM_TDB	OR	ON	2004/09/15 09:30
S63	28	S62 and (semiconductor (semi adj conductor))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT ; IBM_TDB	OR	ON	2004/09/15 11:15

S64	15	S62 and (semiconductor (semi adj conductor)) and (electron beam dose dosage "si-c-si" carbide)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT ; IBM_TDB	OR	ON	2004/09/15 09:58
S65	93501	((electron adj2 beam) same (dose dosage)) "si-c-si" "si-c" (silicon near2 carbide)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT ; IBM_TDB	OR	ON	2004/09/15 10:33
S66	23278	S65 and (semiconductor (semi adj conductor))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT ; IBM_TDB	OR	ON	2004/09/15 10:30
S67	98158	dielectric adj2 constant	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT ; IBM_TDB	OR	ON	2004/09/15 10:30
S68	3133	S66 and S67	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT ; IBM_TDB	OR	ON	2004/09/15 10:30
S69	590151	(film coating dielectric layer) same (semiconductor (semi adj conductor))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT ; IBM_TDB	OR	ON	2004/09/15 10:32
S70	2828	S68 and S69	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT ; IBM_TDB	OR	ON	2004/09/15 10:33
S71	90870	((electron adj2 beam) same (dose dosage)) "si-c-si" (silicon near2 carbide)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT ; IBM_TDB	OR	ON	2004/09/15 11:47
S72	84079	"si-c-si" (silicon near2 carbide)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT ; IBM_TDB	OR	ON	2004/09/15 10:34
S73	3846	S67 and S72	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT ; IBM_TDB	OR	ON	2004/09/15 10:34
S74	2564	S67 and S72 and S69	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT ; IBM_TDB	OR	ON	2004/09/15 10:35

S75	749	(S67 same S72) and S69	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT ; IBM_TDB	OR	ON	2004/09/15 10:36
S76	266	S67 same S72 same S69	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT ; IBM_TDB	OR	ON	2004/09/15 10:54
S77	3	S67 same S72 same S69 and "si-c-si"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT ; IBM_TDB	OR	ON	2004/09/15 10:53
S78	2216	(silicone polysiloxane polyorganosiloxane polydiorganosiloxane organopolysiloxane organosiloxane diorganopolysiloxane siloxane organosilicone) same (silicon near2 carbide)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT ; IBM_TDB	OR	ON	2004/09/15 10:55
S79	126	S78 and S69 and S67	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT ; IBM_TDB	OR	ON	2004/09/15 10:56
S80	6	((electron adj2 beam) same (dose dosage)) and S79	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT ; IBM_TDB	OR	ON	2004/09/15 10:58
S81	528	(dielectric near2 constant) with (silicon near2 carbide)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT ; IBM_TDB	OR	ON	2004/09/15 11:01
S82	410	S69 and S81	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT ; IBM_TDB	OR	ON	2004/09/15 11:04
S83	299	(semiconductor (semi adj conductor) wafer) same (silicon near2 carbide) same (dielectric near2 constant)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT ; IBM_TDB	OR	ON	2004/09/15 11:33
S84	94	(silicon near2 carbide) with (dielectric near2 constant) with ("2.0" "2.1" "2.2" "2.3" "2.4" "2.5" "2.6" "2.7" "2.8" "2.9" "3.0" "2" "3")	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT ; IBM_TDB	OR	ON	2004/09/15 11:31
S85	147	(silicon near2 carbide) with "k" with ("2.0" "2.1" "2.2" "2.3" "2.4" "2.5" "2.6" "2.7" "2.8" "2.9" "3.0" "2" "3")	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT ; IBM_TDB	OR	ON	2004/09/15 11:31

S86	227	S84 S85	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT ; IBM_TDB	OR	ON	2004/09/15 11:32
S87	191	S86 not S83	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT ; IBM_TDB	OR	ON	2004/09/15 11:32
S88	12370	(semiconductor (semi adj conductor) wafer) same (silicon near2 carbide)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT ; IBM_TDB	OR	ON	2004/09/15 11:33
S89	103	S86 and S88	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT ; IBM_TDB	OR	ON	2004/09/15 11:33
S90	7011	((electron adj2 beam) same (dose dosage))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT ; IBM_TDB	OR	ON	2004/09/15 12:08
S91	2	S89 and S90	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT ; IBM_TDB	OR	ON	2004/09/15 11:49
S92	4	S83 and S90	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT ; IBM_TDB	OR	ON	2004/09/15 12:04
S93	2	wo-9936953-\$.did.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT ; IBM_TDB	OR	ON	2004/09/15 12:12
S94	2	wo-9700535-\$.did.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT ; IBM_TDB	OR	ON	2004/09/15 12:06
S95	2	ep-1050601-\$.did.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT ; IBM_TDB	OR	ON	2004/09/15 12:07
S96	2	ep-921561-\$.did.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT ; IBM_TDB	OR	ON	2004/09/15 12:07

S97	11	"6042944".pn. "652922".pn. "6602806".pn. "6235101".pn.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT ; IBM_TDB	OR	ON	2004/09/15 12:08
S98	0	S90 and S97	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT ; IBM_TDB	OR	ON	2004/09/15 12:13
S99	0	(electron adj2 beam) and S97	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT ; IBM_TDB	OR	ON	2004/09/15 12:12
S100	0	electron and S97	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT ; IBM_TDB	OR	ON	2004/09/15 12:09
S101	0	"c-beam" and S97	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT ; IBM_TDB	OR	ON	2004/09/15 12:09
S102	4	"6042994".pn. "6652922".pn.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT ; IBM_TDB	OR	ON	2004/09/15 12:12
S103	4	(electron adj2 beam) and S102	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT ; IBM_TDB	OR	ON	2004/09/15 12:12
S104	2	S90 and S102	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT ; IBM_TDB	OR	ON	2004/09/15 12:13